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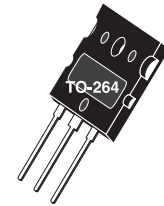
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High Speed PT IGBT

POWER MOS 8® is a high speed Punch-Through switch-mode IGBT. Low E_{off} is achieved through leading technology silicon design and lifetime control processes. A reduced $E_{off} - V_{CE(ON)}$ tradeoff results in superior efficiency compared to other IGBT technologies. Low gate charge and a greatly reduced ratio of C_{res}/C_{ies} provide excellent noise immunity, short delay times and simple gate drive. The intrinsic chip gate resistance and capacitance of the poly-silicone gate structure help control di/dt during switching, resulting in low EMI, even when switching at high frequency.


APT80GA60LD40


Combi (IGBT and Diode)

FEATURES

- Fast switching with low EMI
- Very Low E_{off} for maximum efficiency
- Ultra low C_{res} for improved noise immunity
- Low conduction loss
- Low gate charge
- Increased intrinsic gate resistance for low EMI
- RoHS compliant 

TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- High power PFC boost
- Welding
- UPS, solar, and other inverters
- High frequency, high efficiency industrial

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector Emitter Voltage	600	V
I_{C1}	Continuous Collector Current @ $T_c = 25^\circ\text{C}$	143	A
I_{C2}	Continuous Collector Current @ $T_c = 100^\circ\text{C}$	80	
I_{CM}	Pulsed Collector Current ¹	240	
V_{GE}	Gate-Emitter Voltage ²	± 30	V
P_D	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	625	W
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	240A @ 600V	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature for Soldering: 0.063" from Case for 10 Seconds	300	

Static Characteristics

 $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1.0mA$	600			V
$V_{CE(on)}$	Collector-Emitter On Voltage	$V_{GE} = 15V, I_C = 47A$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.0 1.9	2.5	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3	4.5	6	
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 600V, V_{GE} = 0V$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			275 3000	μA
I_{GES}	Gate-Emitter Leakage Current	$V_{GS} = \pm 30V$			± 100	nA

Dynamic Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

APT80GA60LD40

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{MHz}$		6390		pF	
C_{oes}	Output Capacitance			580			
C_{res}	Reverse Transfer Capacitance			63			
Q_g^3	Total Gate Charge	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 47A$		230		nC	
Q_{ge}	Gate-Emitter Charge			40			
Q_{gc}	Gate-Collector Charge			78			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 4.7\Omega^4, V_{GE} = 15V,$ $L = 100\mu\text{H}, V_{CE} = 600V$	240			A	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +25^\circ\text{C}$		23		ns	
t_r	Current Rise Time			27			
$t_{d(off)}$	Turn-Off Delay Time			158			
t_f	Current Fall Time			78			
E_{on2}	Turn-On Switching Energy				840		μJ
E_{off}^6	Turn-Off Switching Energy				751		
$t_{d(on)}$	Turn-On Delay Time		Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +125^\circ\text{C}$		21		ns
t_r	Current Rise Time				31		
$t_{d(off)}$	Turn-Off Delay Time			194			
t_f	Current Fall Time			132			
E_{on2}	Turn-On Switching Energy				1275		μJ
E_{off}^6	Turn-Off Switching Energy				1112		

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)	-	-	0.2	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case Thermal Resistance (Diode)			.67	
W_T	Package Weight	-	6.1	-	g
Torque	Mounting Torque (TO-264 Package), 4-40 or M3 screw			10	in-lbf

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width < $380\mu\text{s}$, duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves

APT80GA60LD40

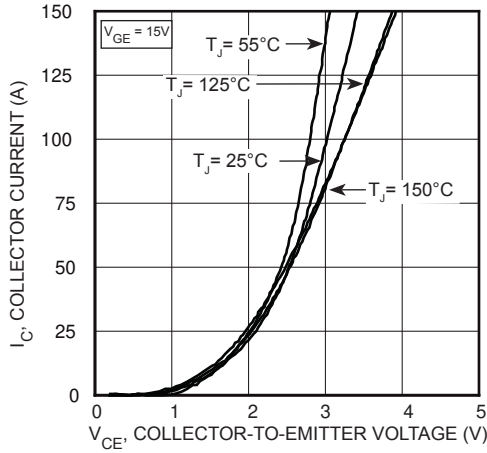


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

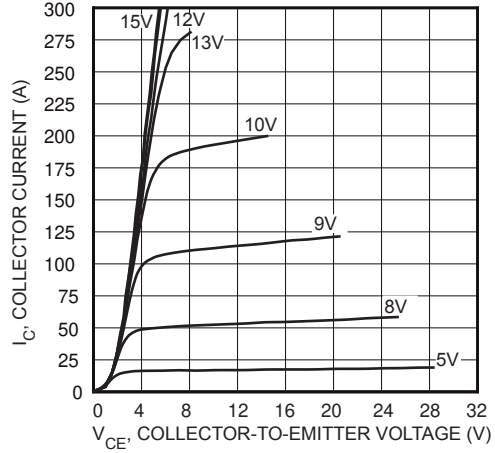


FIGURE 2, Output Characteristics ($T_J = 25^\circ\text{C}$)

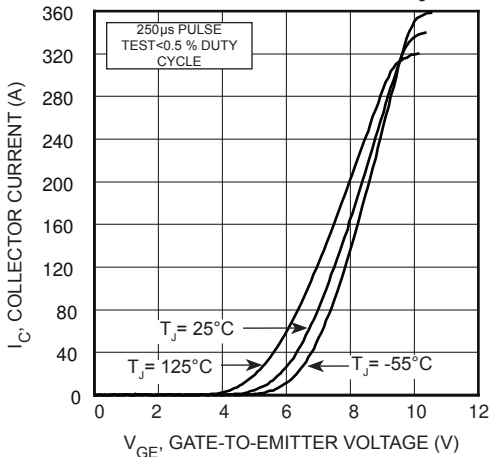


FIGURE 3, Transfer Characteristics

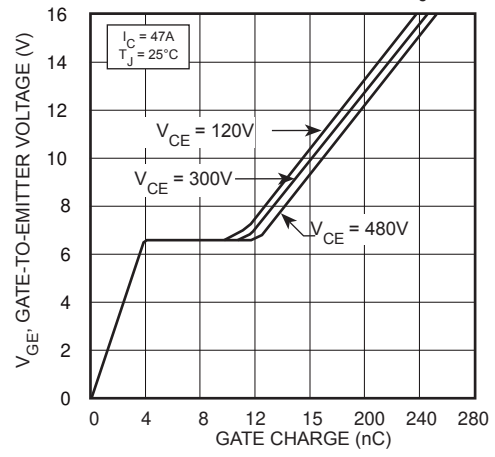


FIGURE 4, Gate charge

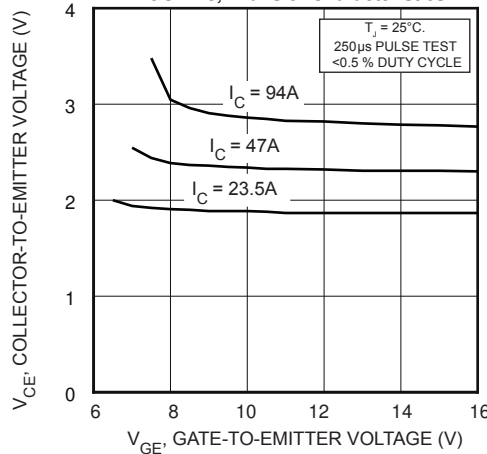


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

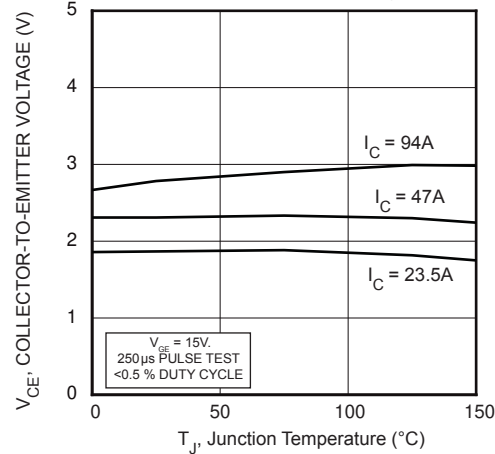


FIGURE 6, On State Voltage vs Junction Temperature

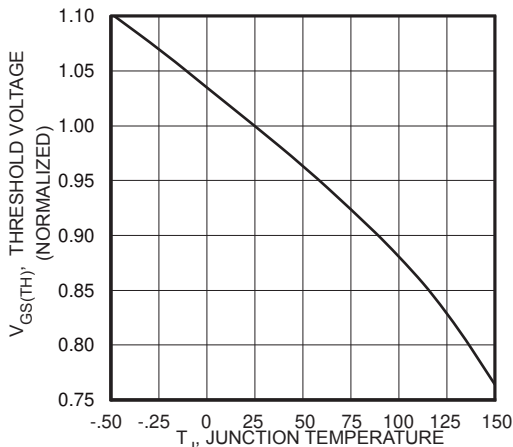


FIGURE 7, Threshold Voltage vs Junction Temperature

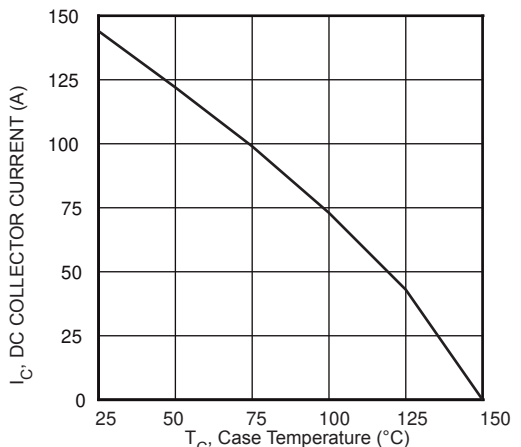


FIGURE 8, DC Collector Current vs Case Temperature

Typical Performance Curves

APT80GA60LD40

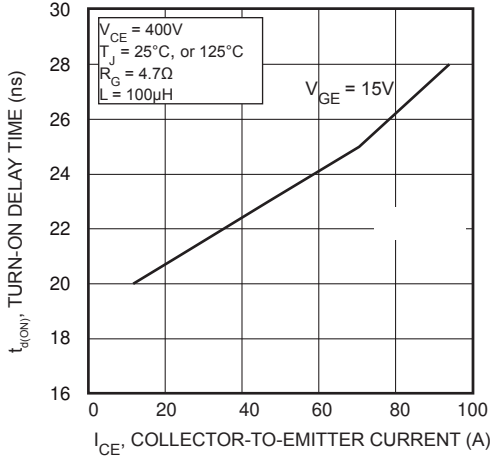


FIGURE 9, Turn-On Delay Time vs Collector Current

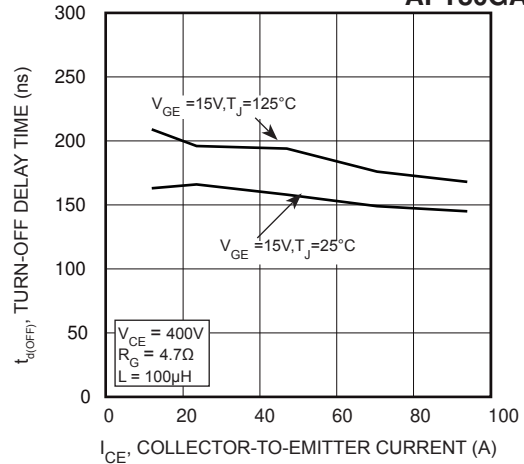


FIGURE 10, Turn-Off Delay Time vs Collector Current

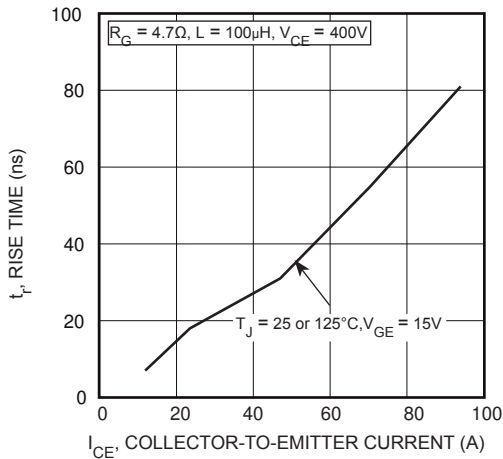


FIGURE 11, Current Rise Time vs Collector Current

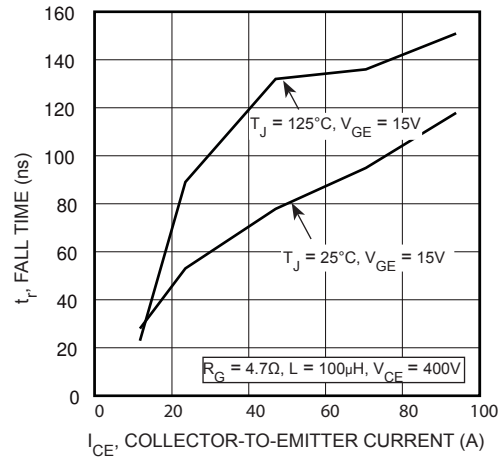


FIGURE 12, Current Fall Time vs Collector Current

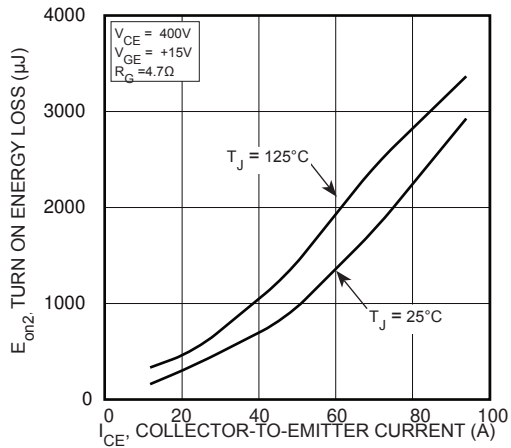


FIGURE 13, Turn-On Energy Loss vs Collector Current

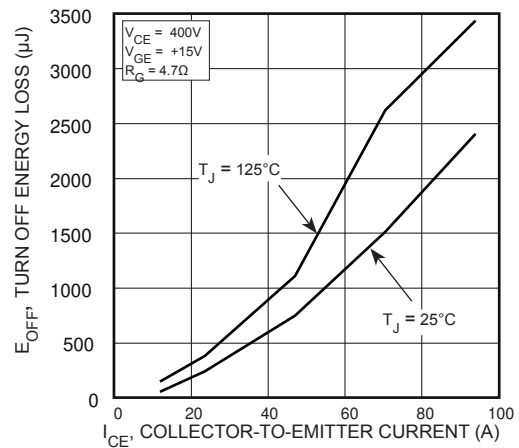


FIGURE 14, Turn-Off Energy Loss vs Collector Current

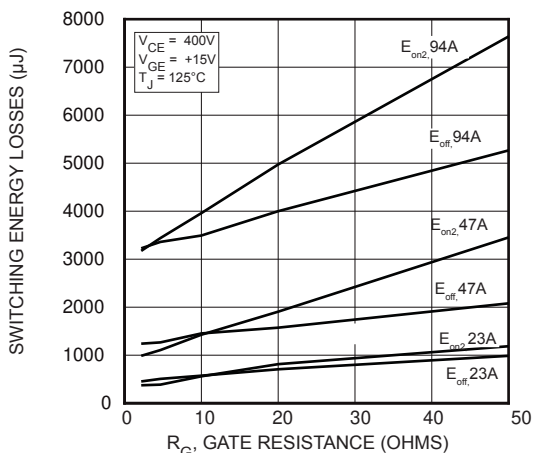


FIGURE 15, Switching Energy Losses vs Gate Resistance

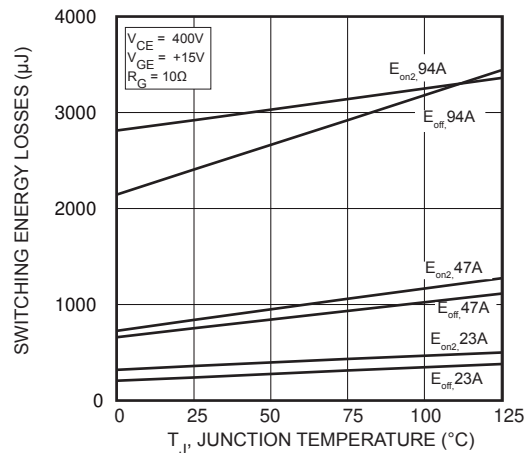


FIGURE 16, Switching Energy Losses vs Junction Temperature

Typical Performance Curves

APT80GA60LD40

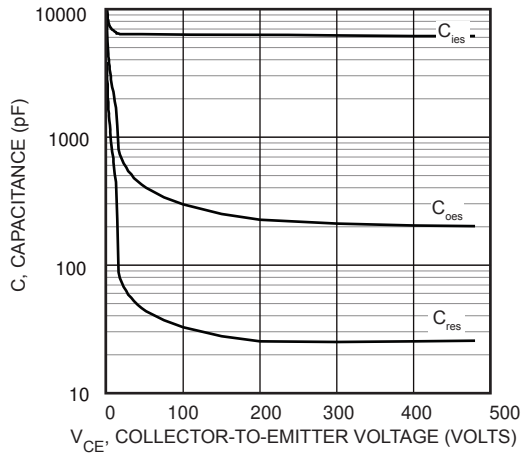


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

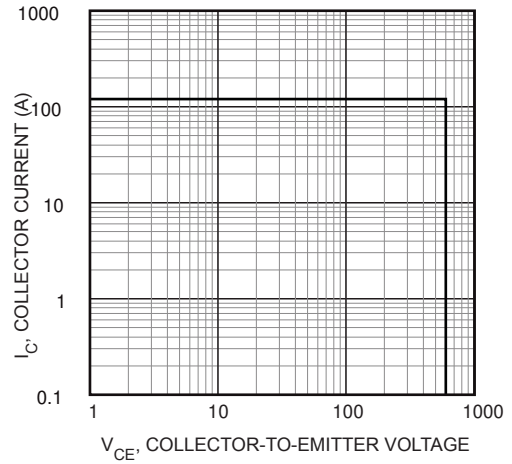


FIGURE 18, Minimum Switching Safe Operating Area

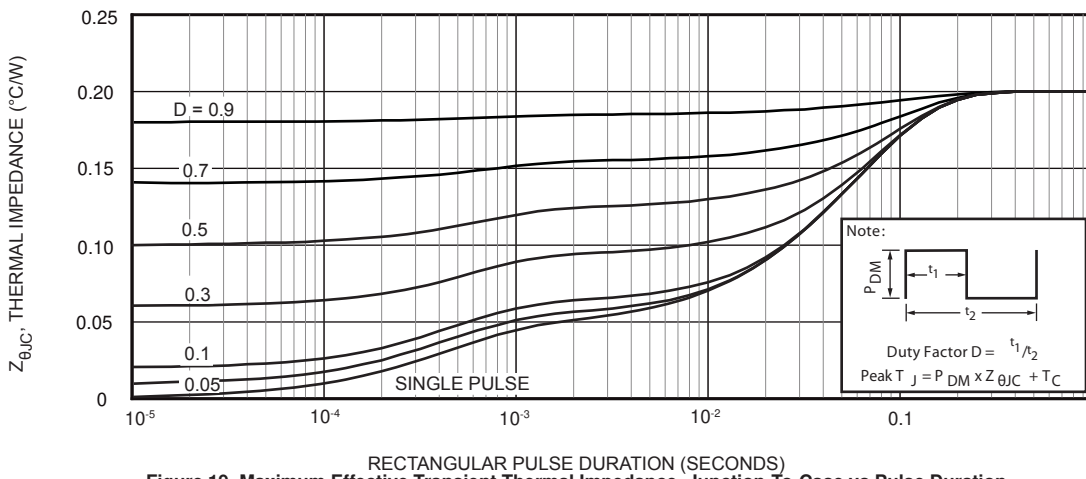


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

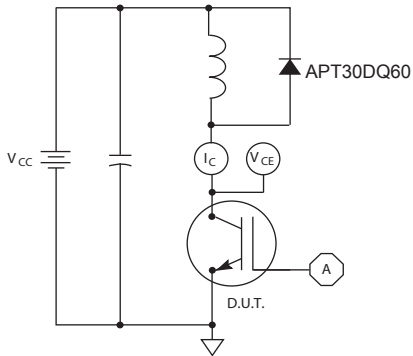


Figure 20, Inductive Switching Test Circuit

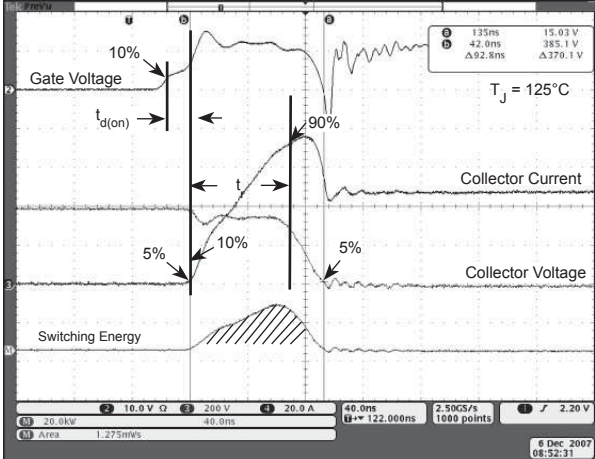


Figure 21, Turn-on Switching Waveforms and Definitions

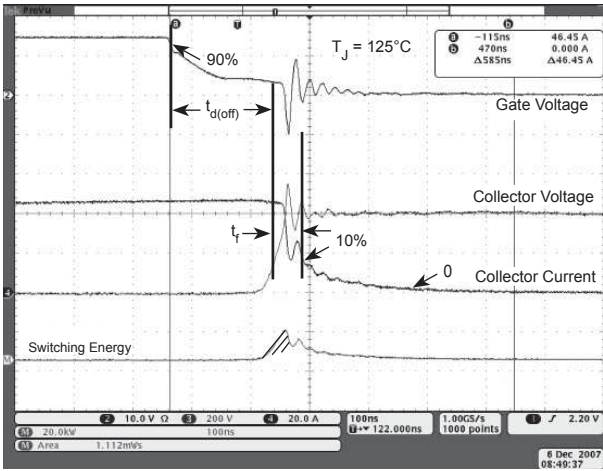


Figure 22, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT80GA60LD40	Unit
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 111^\circ\text{C}$, Duty Cycle = 0.5)	40	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	63	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3 ms)	320	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Type	Max	Unit
V_F	Forward Voltage		$I_F = 40\text{A}$	2.0	Volts
			$I_F = 80\text{A}$	2.5	
			$I_F = 40\text{A}, T_J = 125^\circ\text{C}$	1.7	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	22	-	ns
t_{rr}	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	25	-	nAmps
Q_{rr}	Reverse Recovery Charge		-	35	-	
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	
t_{rr}	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	160	-	ns
Q_{rr}	Reverse Recovery Charge		-	480	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	85	-	ns
Q_{rr}	Reverse Recovery Charge		-	920	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	20	-	Amps

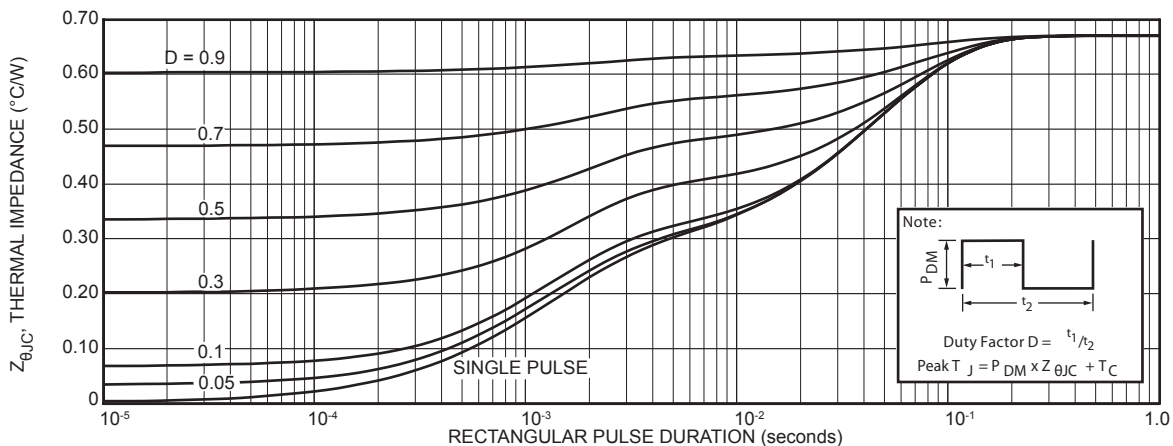


FIGURE 23, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

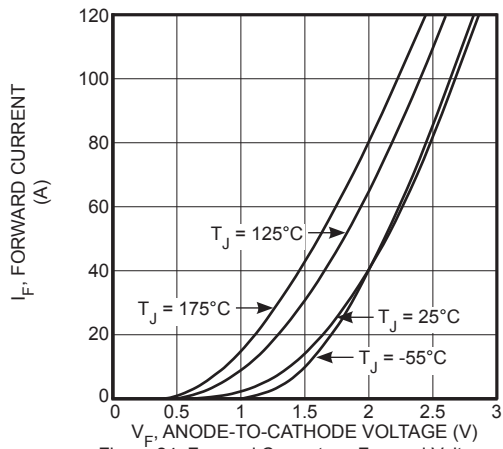


Figure 24. Forward Current vs. Forward Voltage

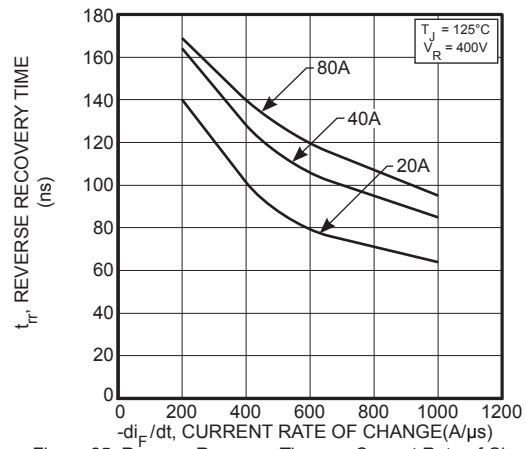


Figure 25. Reverse Recovery Time vs. Current Rate of Change

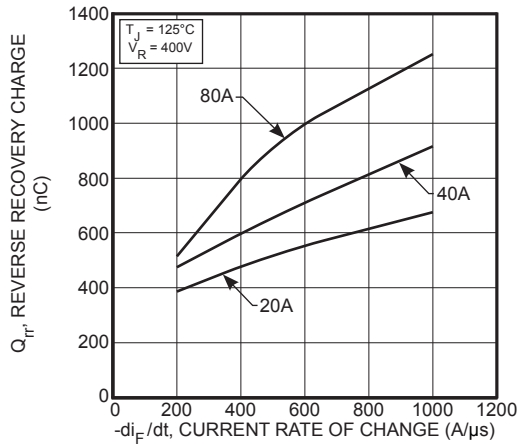


Figure 26. Reverse Recovery Charge vs. Current Rate of Change

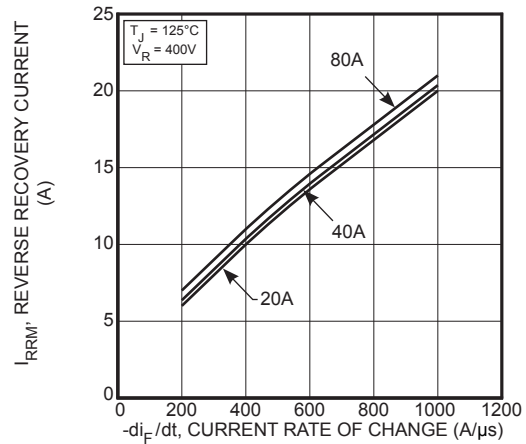


Figure 27. Reverse Recovery Current vs. Current Rate of Change

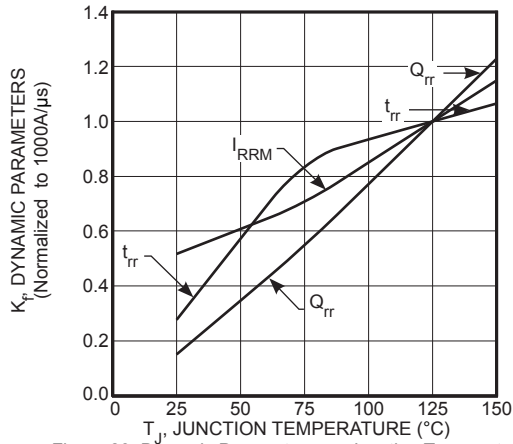


Figure 28. Dynamic Parameters vs. Junction Temperature

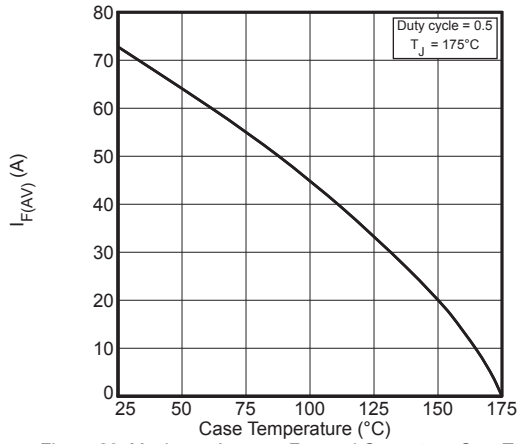


Figure 29. Maximum Average Forward Current vs. Case Temperature

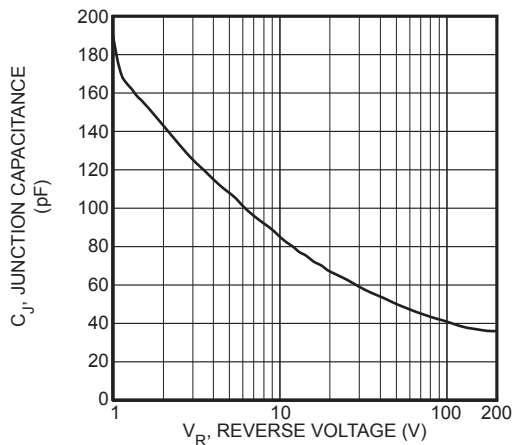


Figure 30. Junction Capacitance vs. Reverse Voltage

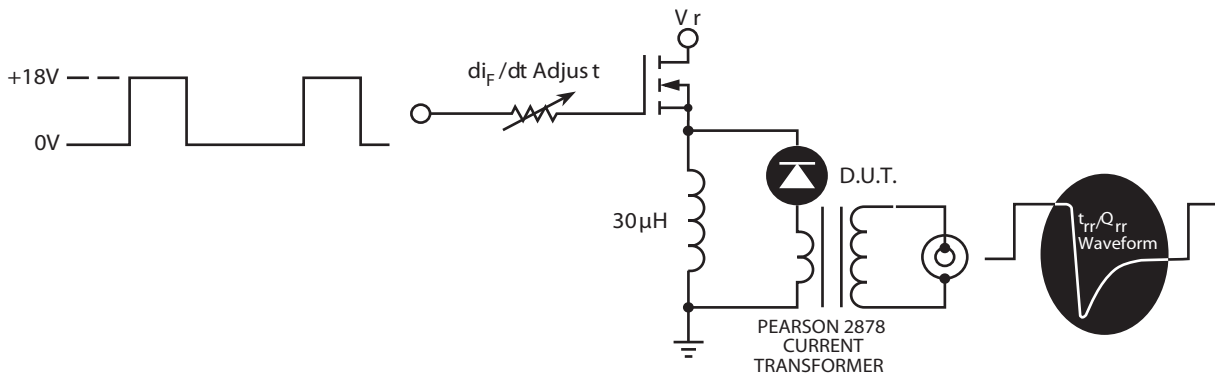


Figure 31. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current
- 4 t_{rr} - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{RR} .

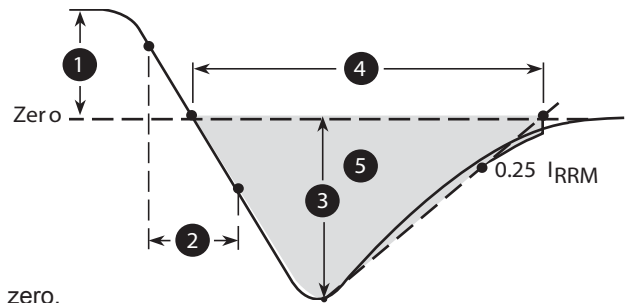


Figure 32. Diode Reverse Recovery Waveform Definition

TO-264 (L) Package Outline

